

High Speed, High Gain Bipolar NPN Power Transistor with Integrated Collector-Emitter Diode and Built-in Efficient Antisaturation Network

The MJE18002D2 use a newly developed technology, so called H2BIP*, to design the state of art transistor dedicated to the Electronic Light Ballast and PFC** circuit.

The main advantages brought by these new transistors are:

- Improved Global Efficiency Due to the Low Base Drive Requirements
- DC Current Gain Typically Centered at 45
- Extremely Low Storage Time Variation, Thanks to the Antisaturation Network
- Easy to Use Thanks to the Integrated Collector/Emitter Diode

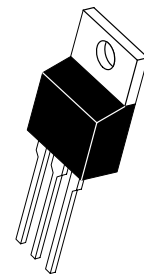
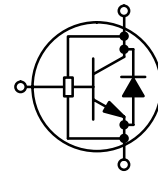
The ON Semiconductor Six Sigma philosophy provides tight and reproducible parameter distribution.

* High speed High gain Bipolar transistor

** Power Factor Control

MJE18002D2

POWER TRANSISTORS
2 AMPERES
1000 VOLTS
50 WATTS



CASE 221A-00
TO-220AB

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Sustaining Voltage	V_{CEO}	450	Vdc
Collector-Base Breakdown Voltage	V_{CBO}	1000	Vdc
Collector-Emitter Breakdown Voltage	V_{CES}	1000	Vdc
Emitter-Base Voltage	V_{EBO}	12	Vdc
Collector Current — Continuous — Peak (1)	I_C I_{CM}	2 5	Adc
Base Current — Continuous — Peak (1)	I_B I_{BM}	1 2	Adc
*Total Device Dissipation @ $T_C = 25^\circ\text{C}$ *Derate above 25°C	P_D	50 0.4	Watt W/ $^\circ\text{C}$
Operating and Storage Temperature	T_J, T_{stg}	-65 to 150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Thermal Resistance — Junction to Case — Junction to Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.5 62.5	$^\circ\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes: 1/8" from case for 5 seconds	T_L	260	$^\circ\text{C}$

(1) Pulse Test: Pulse Width = 5 ms, Duty Cycle \leq 10%.

MJE1800D2

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

OFF CHARACTERISTICS

Collector–Emitter Sustaining Voltage ($I_C = 100\text{ mA}$, $L = 25\text{ mH}$)	$V_{CEO(sus)}$	450	570		Vdc
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CEO}$, $I_B = 0$)	I_{CEO}			100	μA dc
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CES}$, $V_{EB} = 0$) ($V_{CE} = 500\text{ V}$, $V_{EB} = 0$)	I_{CES}			100 500 100	μA dc
Emitter–Cutoff Current ($V_{EB} = 10\text{ Vdc}$, $I_C = 0$)	I_{EBO}			100	μA dc

ON CHARACTERISTICS

Base–Emitter Saturation Voltage ($I_C = 0.4\text{ Adc}$, $I_B = 40\text{ mA}$ dc) ($I_C = 1\text{ Adc}$, $I_B = 0.2\text{ Adc}$)	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	$V_{BE(sat)}$		0.78 0.87	1 1.1	Vdc
Collector–Emitter Saturation Voltage ($I_C = 0.4\text{ Adc}$, $I_B = 40\text{ mA}$ dc) ($I_C = 1\text{ Adc}$, $I_B = 0.2\text{ Adc}$)	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$ @ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	$V_{CE(sat)}$		0.36 0.5 0.4 0.65	0.6 1 0.75 1.2	Vdc
DC Current Gain ($I_C = 0.4\text{ Adc}$, $V_{CE} = 1\text{ Vdc}$) ($I_C = 1\text{ Adc}$, $V_{CE} = 1\text{ Vdc}$)	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$ @ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	h_{FE}	14 8 6 4	25 15 10 6		—

DYNAMIC CHARACTERISTICS

Current Gain Bandwidth ($I_C = 0.5\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1\text{ MHz}$)	f_T		13		MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1\text{ MHz}$)	C_{ob}		50	100	pF
Input Capacitance ($V_{EB} = 8\text{ Vdc}$)	C_{ib}		340	500	pF

DIODE CHARACTERISTICS

Forward Diode Voltage ($I_{EC} = 1\text{ Adc}$) ($I_{EC} = 0.2\text{ Adc}$) ($I_{EC} = 0.4\text{ Adc}$)	@ $T_C = 25^\circ\text{C}$ @ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$ @ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	V_{EC}		1.2 0.9 0.6 1 0.6	1.5 1.2 1.3	V
Forward Recovery Time ($I_F = 0.2\text{ Adc}$, $di/dt = 10\text{ A}/\mu\text{s}$) ($I_F = 0.4\text{ Adc}$, $di/dt = 10\text{ A}/\mu\text{s}$) ($I_F = 1\text{ Adc}$, $di/dt = 10\text{ A}/\mu\text{s}$)	@ $T_C = 25^\circ\text{C}$ @ $T_C = 25^\circ\text{C}$ @ $T_C = 25^\circ\text{C}$	t_{fr}		540 517 480		ns

MJE18002D2

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
----------------	--------	-----	-----	-----	------

SWITCHING CHARACTERISTICS: Resistive Load ($D.C. \leq 10\%$, Pulse Width = 20 μs)

Turn-on Time	$I_C = 1 \text{ Adc}$, $I_{B1} = 0.2 \text{ Adc}$ $I_{B2} = 0.5 \text{ Adc}$ $V_{CC} = 300 \text{ Vdc}$	@ $T_C = 25^\circ\text{C}$	t_{on}		100	150	ns
		@ $T_C = 125^\circ\text{C}$			94		
Turn-off Time		@ $T_C = 25^\circ\text{C}$	t_{off}	0.95	1.5	1.25	μs
		@ $T_C = 125^\circ\text{C}$					

SWITCHING CHARACTERISTICS: Inductive Load ($V_{clamp} = 300 \text{ V}$, $V_{CC} = 15 \text{ V}$, $L = 200 \mu\text{H}$)

Fall Time	$I_C = 0.4 \text{ Adc}$ $I_{B1} = 40 \text{ mAdc}$ $I_{B2} = 0.2 \text{ Adc}$	@ $T_C = 25^\circ\text{C}$	t_f		130	175	ns
		@ $T_C = 125^\circ\text{C}$			120		
Storage Time		@ $T_C = 25^\circ\text{C}$	t_s		0.55	0.65	μs
		@ $T_C = 125^\circ\text{C}$			0.7		
Crossover Time		@ $T_C = 25^\circ\text{C}$	t_c		110	175	ns
		@ $T_C = 125^\circ\text{C}$			100		
Fall Time	$I_C = 0.8 \text{ Adc}$ $I_{B1} = 160 \text{ mAdc}$ $I_{B2} = 160 \text{ mAdc}$	@ $T_C = 25^\circ\text{C}$	t_f		130	175	ns
		@ $T_C = 125^\circ\text{C}$			140		
Storage Time		@ $T_C = 25^\circ\text{C}$	t_s	2.1	3	2.4	μs
		@ $T_C = 125^\circ\text{C}$					
Crossover Time		@ $T_C = 25^\circ\text{C}$	t_c		275	350	ns
		@ $T_C = 125^\circ\text{C}$			350		
Fall Time	$I_C = 1 \text{ Adc}$ $I_{B1} = 0.2 \text{ Adc}$ $I_{B2} = 0.5 \text{ Adc}$	@ $T_C = 25^\circ\text{C}$	t_f		100	150	ns
		@ $T_C = 125^\circ\text{C}$			100		
Storage Time		@ $T_C = 25^\circ\text{C}$	t_s		1.05	1.2	μs
		@ $T_C = 125^\circ\text{C}$			1.45		
Crossover Time		@ $T_C = 25^\circ\text{C}$	t_c		100	150	ns
		@ $T_C = 125^\circ\text{C}$			115		

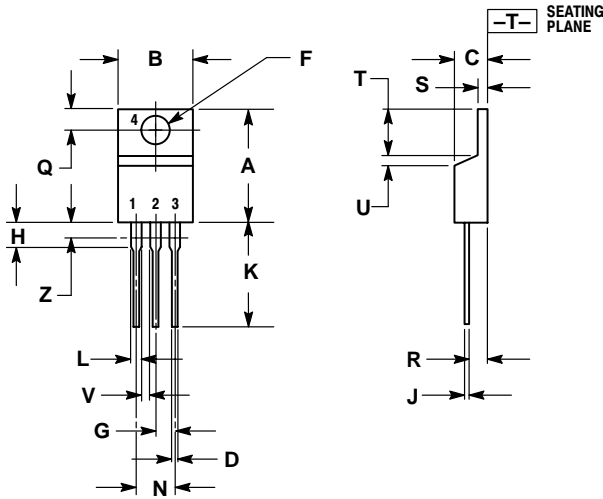
DYNAMIC SATURATION VOLTAGE

Dynamic Saturation Voltage: Determined 1 μs and 3 μs respectively after rising I_{B1} reaches 90% of final I_{B1}	$I_C = 0.4 \text{ Adc}$ $I_{B1} = 40 \text{ mA}$ $V_{CC} = 300 \text{ V}$	@ 1 μs	@ $T_C = 25^\circ\text{C}$	$V_{CE(dsat)}$		7.4		V
		@ 3 μs	@ $T_C = 25^\circ\text{C}$			2.5		
	$I_C = 1 \text{ Adc}$ $I_{B1} = 0.2 \text{ A}$ $V_{CC} = 300 \text{ V}$	@ 1 μs	@ $T_C = 25^\circ\text{C}$			11.7		
		@ 3 μs	@ $T_C = 25^\circ\text{C}$			1.3		

MJE18002D2

PACKAGE DIMENSIONS


TO-220AB CASE 221A-09 ISSUE AA



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

NORTH AMERICA Literature Fulfillment:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: ONlit@hibbertco.com
Fax Response Line: 303-675-2167 or 800-344-3810 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor – European Support

German Phone: (+1) 303-308-7140 (Mon-Fri 2:30pm to 7:00pm CET)
Email: ONlit-german@hibbertco.com
French Phone: (+1) 303-308-7141 (Mon-Fri 2:00pm to 7:00pm CET)
Email: ONlit-french@hibbertco.com
English Phone: (+1) 303-308-7142 (Mon-Fri 12:00pm to 5:00pm GMT)
Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS*: 00-800-4422-3781

*Available from Germany, France, Italy, UK, Ireland

CENTRAL/SOUTH AMERICA:

Spanish Phone: 303-308-7143 (Mon-Fri 8:00am to 5:00pm MST)
Email: ONlit-spanish@hibbertco.com
Toll-Free from Mexico: Dial 01-800-288-2872 for Access –
then Dial 866-297-9322

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support

Phone: 1-303-675-2121 (Tue-Fri 9:00am to 1:00pm, Hong Kong Time)
Toll Free from Hong Kong & Singapore:
001-800-4422-3781
Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center

4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031
Phone: 81-3-5740-2700
Email: r14525@onsemi.com

ON Semiconductor Website: <http://onsemi.com>

For additional information, please contact your local Sales Representative.